

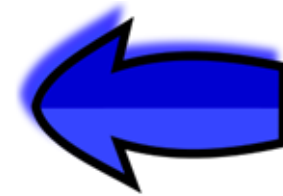


Chapter 7: A Primer On Digital Logic

Basic Computer Architecture

Outline

*Transistors and Gates



*Combinational Logic

* Sequential Logic

* SRAM/ DRAM Cells

Disclaimer: This chapter is only to



get a high level overview ...

- * We assume some **background** in logic gates, transistors, combinational and sequential logic
- * The **aim** of this chapter is to only provide a high level overview
- * For a **deeper** understanding consult any of the classic textbooks on digital logic

Atoms and Molecules of Circuits

The Transistor

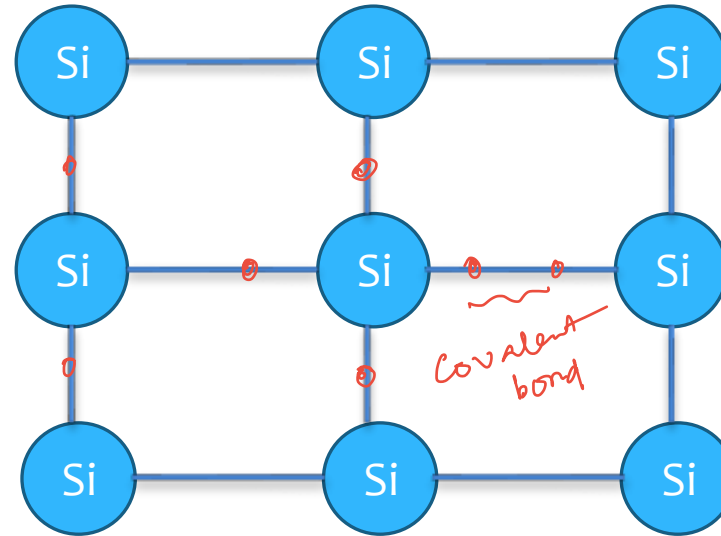


- It is just a **switch**.
- It is either switched **on** (current can flow), or switched **off** (no current flow)

How is a Transistor Made?

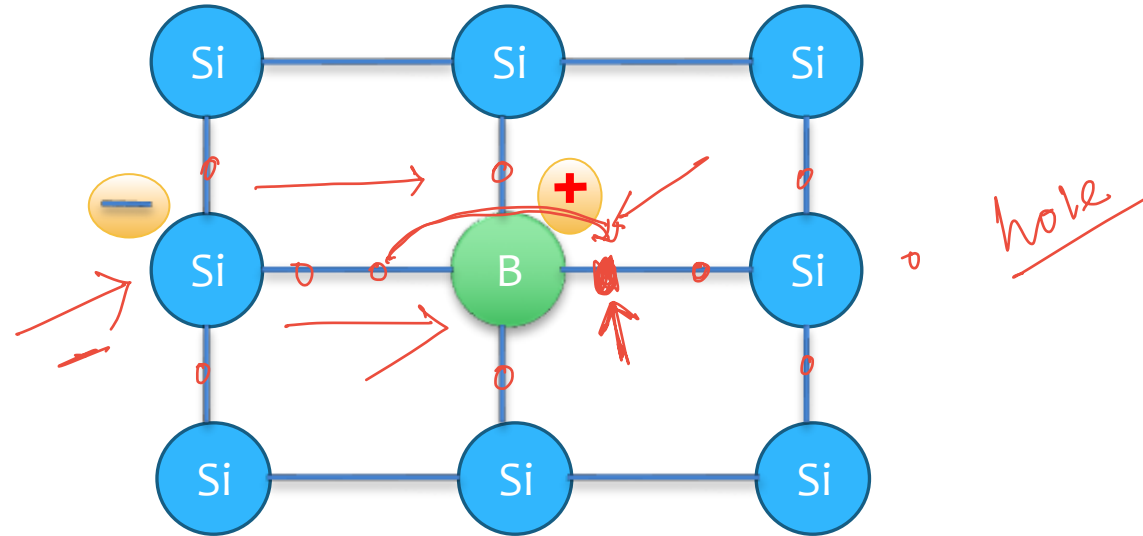
- * It is made of **Silicon**
 - * Silicon is a semi-conductor (neither conductor or insulator).
 - * We can change its properties:
 - * Add a little bit of impurities → doping
- * Dope it with Group III **elements (3 valence electrons)**
 - * Boron, Aluminum and Gallium
 - * It is called a **p-type** semiconductor
- * Or, dope it with Group V **elements (5 valence electrons)**
 - * Phosphorus or Arsenic
 - * It is called a **n-type** semiconductor

Silicon Lattice



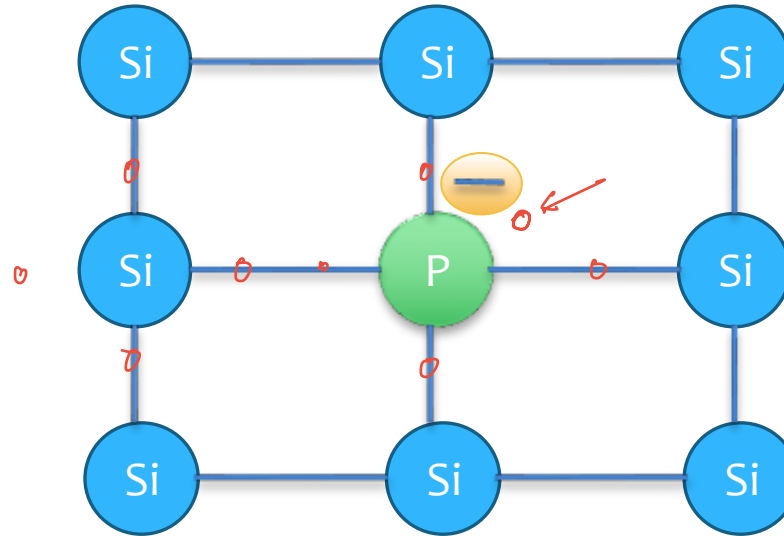
- * This is a typical silicon lattice. Each Si atom is connected to 4 other atoms via covalent bond

P-Type Doping



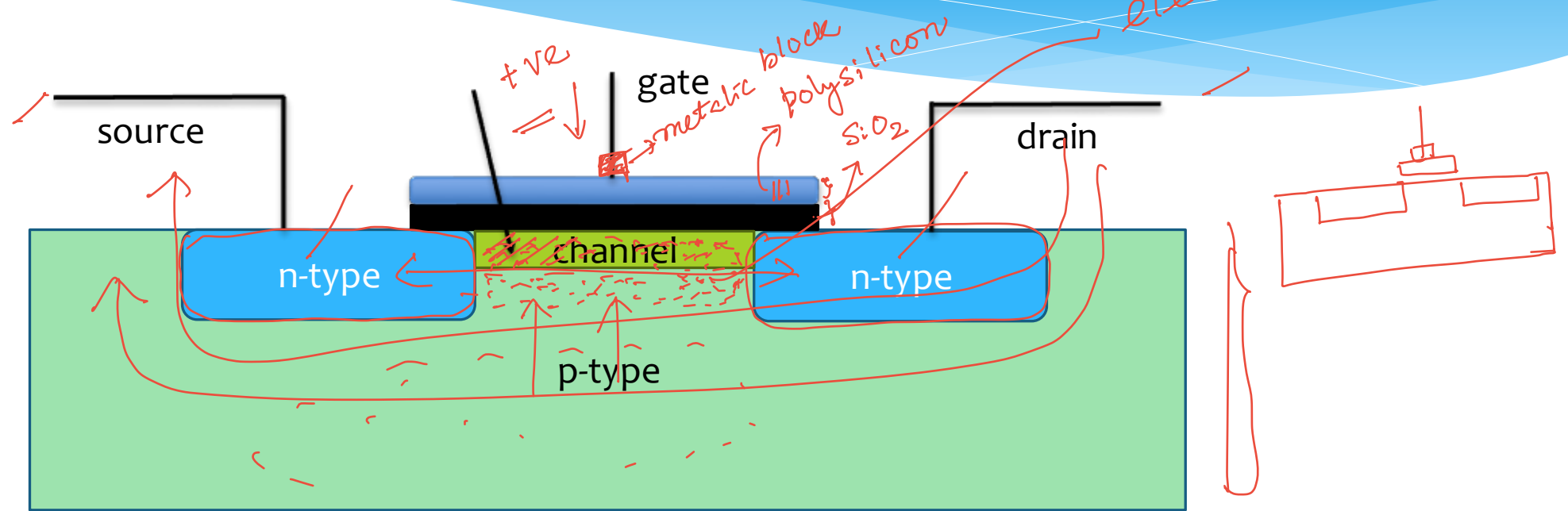
- * If there is a Boron atom in the **lattice**. It will create bonds with the rest of the atoms.
- * There will be one less electron (**hole**)
- * Holes can **flow**. They are associated with +ve charge. (see the animation)

N-Type Doping



- * If there is a Phosphorus atom in the **lattice**. It will create bonds with the rest of the atoms.
- * There will be one more electron (**electron**)
- * Electrons can **flow**. They are associated with -ve charge. (see the animation)

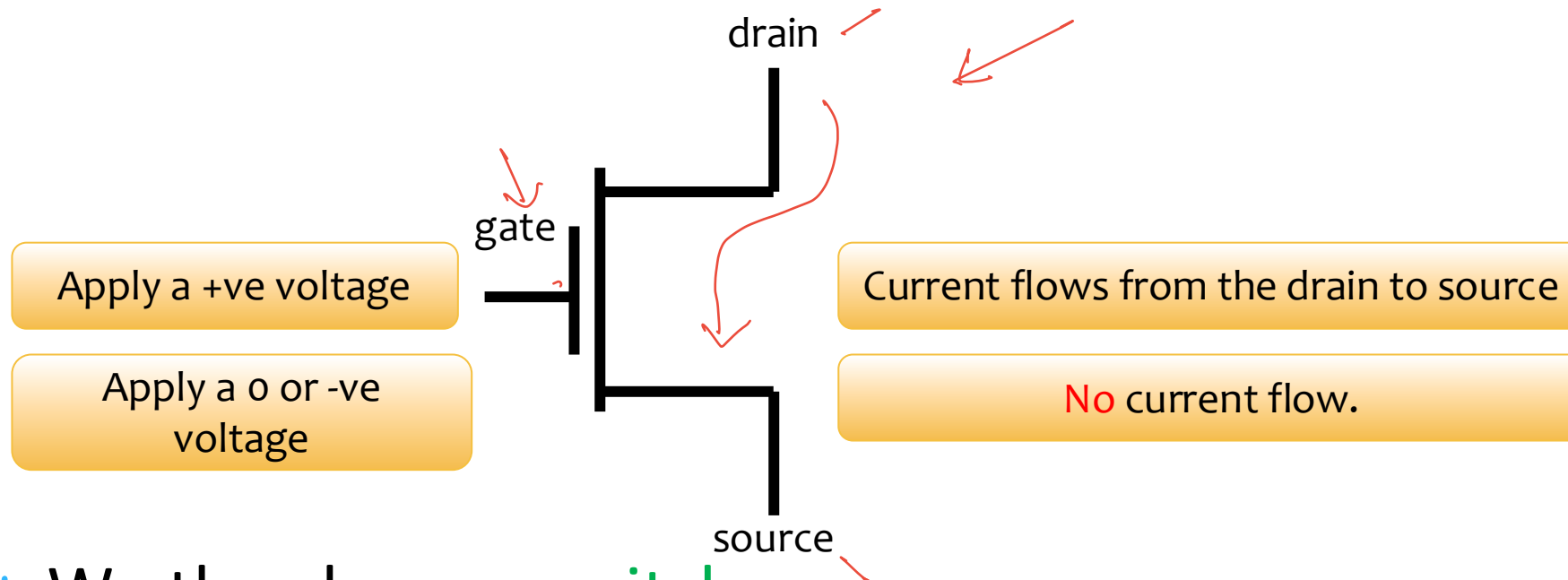
Let us make a transistor.



- * NMOS transistor → Put two **n-type** wells in a **p-type** substrate
- * Now, assume that we apply **+ve** charge to the gate.
- * Channel → This forms because electrons move towards the positive charge. Forms a conductive layer that can conduct **current**.

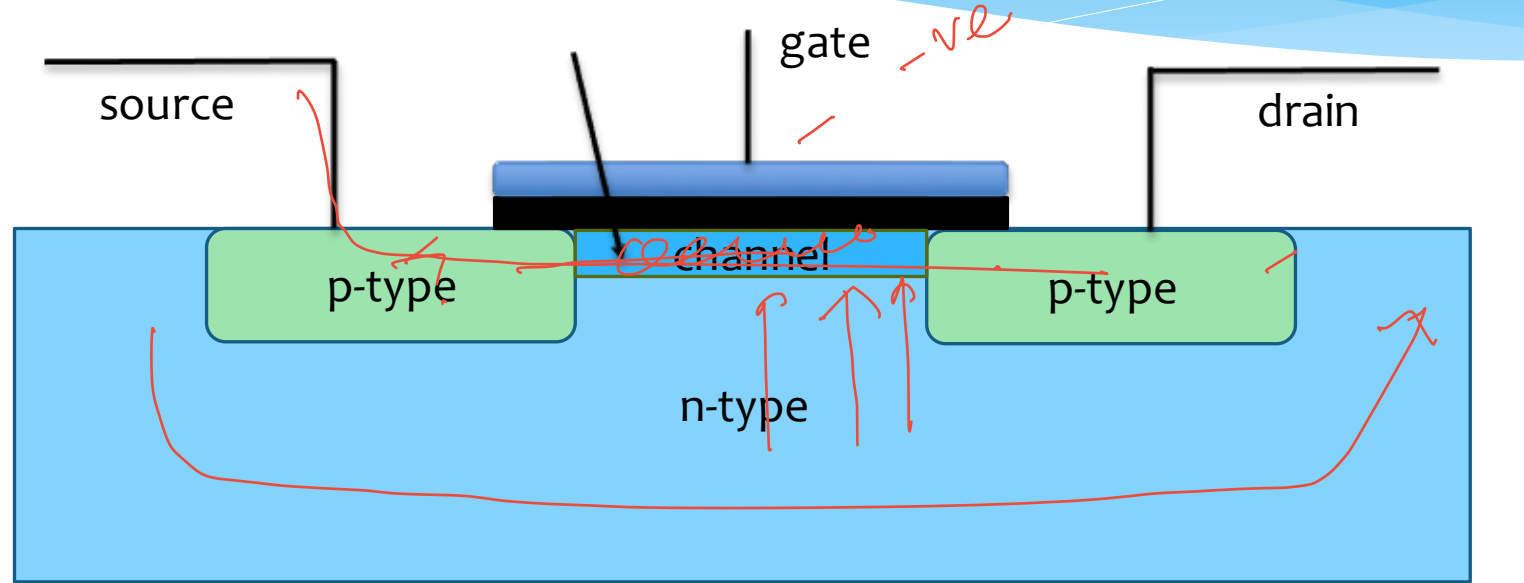
NMOS Transistor

Metal-Oxide-Semiconductor



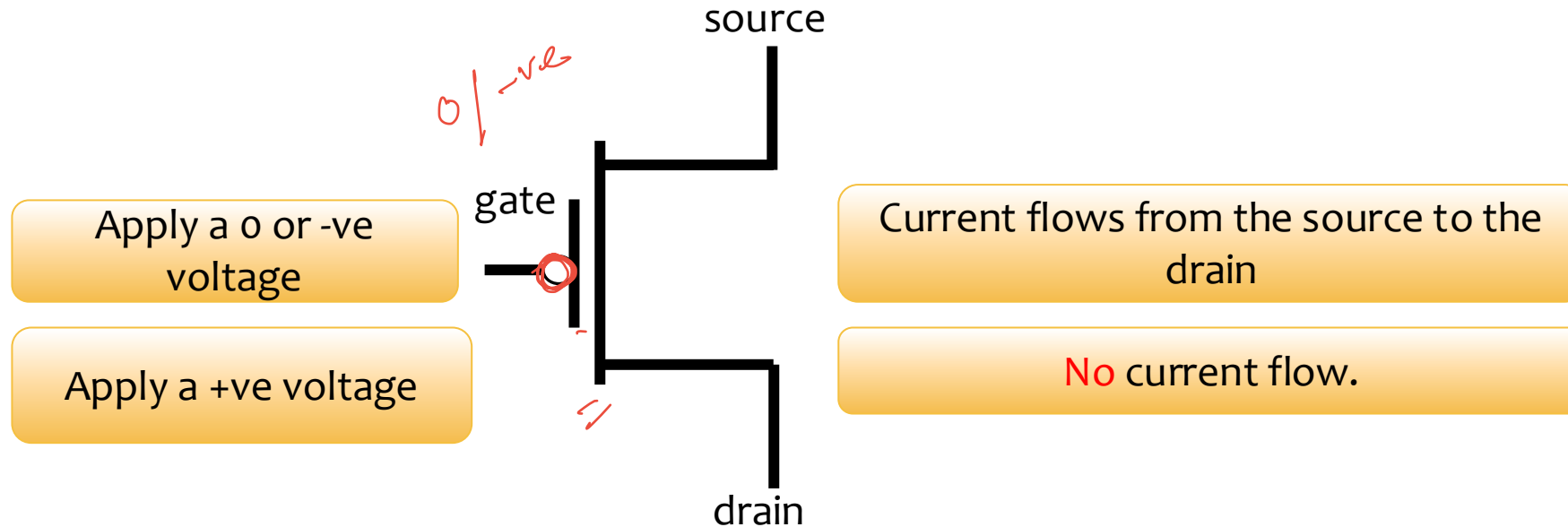
- * We thus have a **switch**
 - * Apply a **+ve** voltage at the gate → make the transistor conduct
 - * Apply a **-ve** or 0 voltage at the gate → transistor is off (no current flow across it)

PMOS Transistor



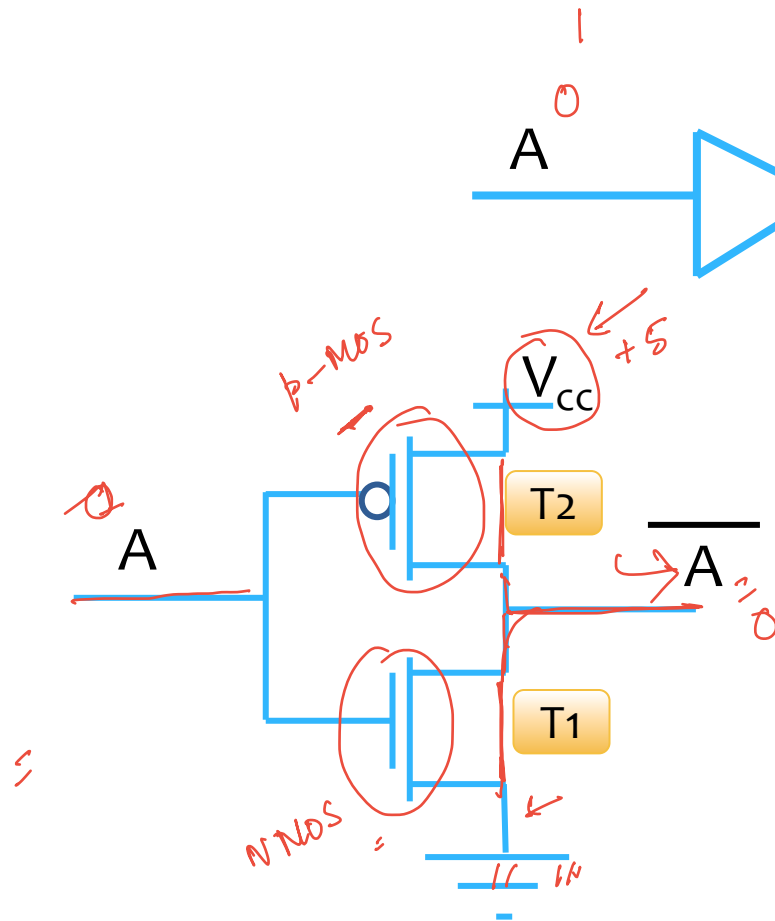
- * PMOS transistor → Put two **p-type** wells in an **n-type** substrate
- * Now, assume we apply **0 or -ve** charge to the gate.
- * Channel → This forms because holes move towards the gate. This channel can conduct **current**.

PMOS Transistor



- * We thus have a **switch**
 - * Apply a **+ve** voltage at the gate → transistor is off (no current flow across it)
 - * Apply a **-ve** or 0 voltage at the gate → transistor conducts

Let us make an inverter

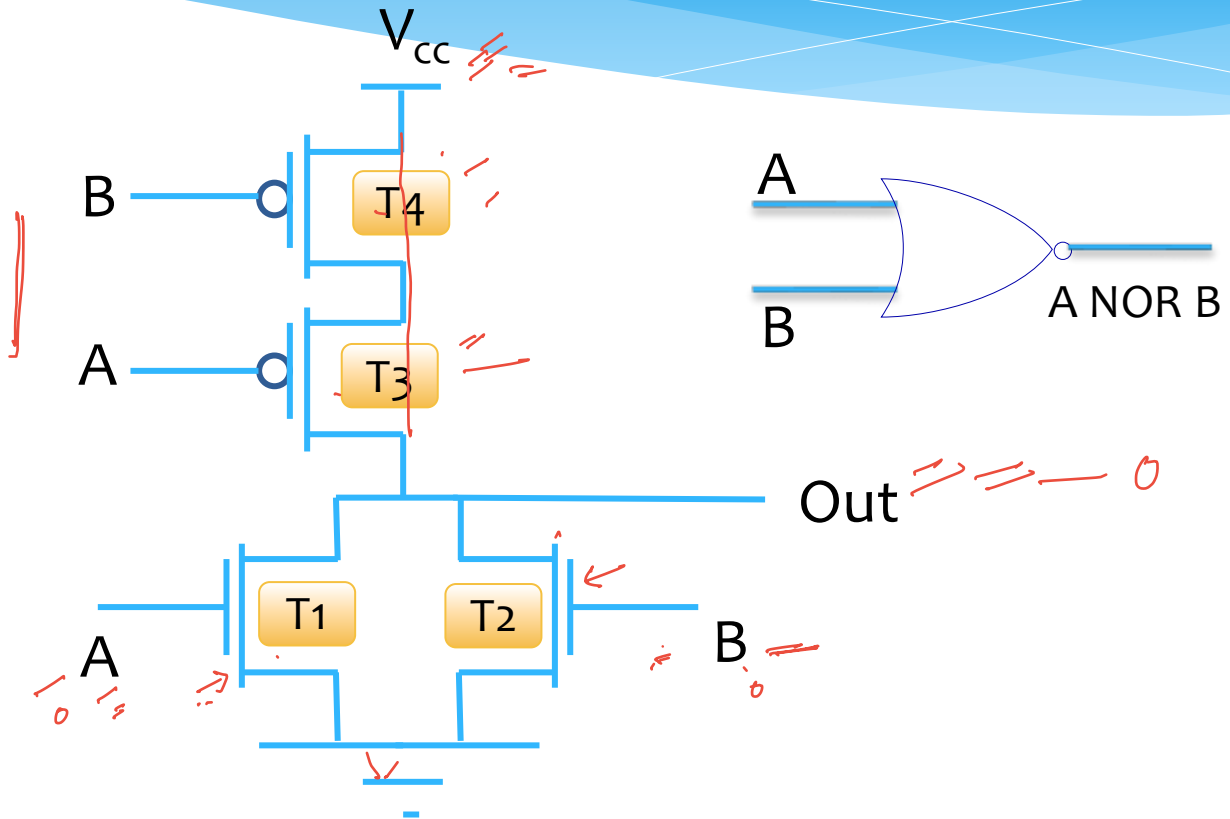
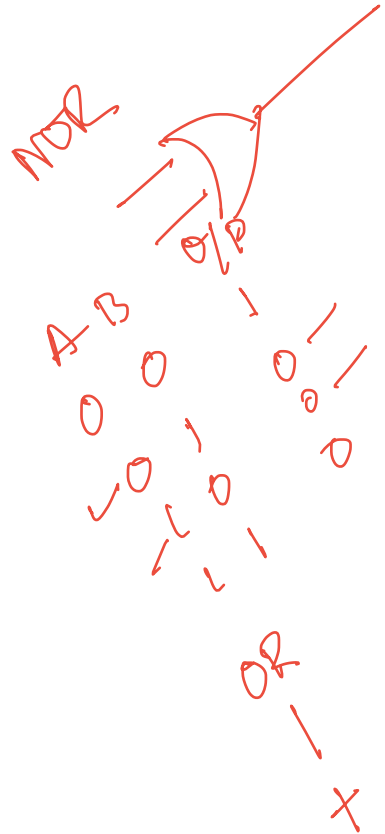


If $A = 1$ (+ve voltage)
T1 is on, T2 is off
Thus, the output will be connected to the ground, and it will be a logical 0

If $A = 0$ (0 voltage)
T1 is off, T2 is on
Thus, the output will be connected to the supply (V_{CC}), and it will be a logical 1

Complementary Metal-Oxide-Semiconductor

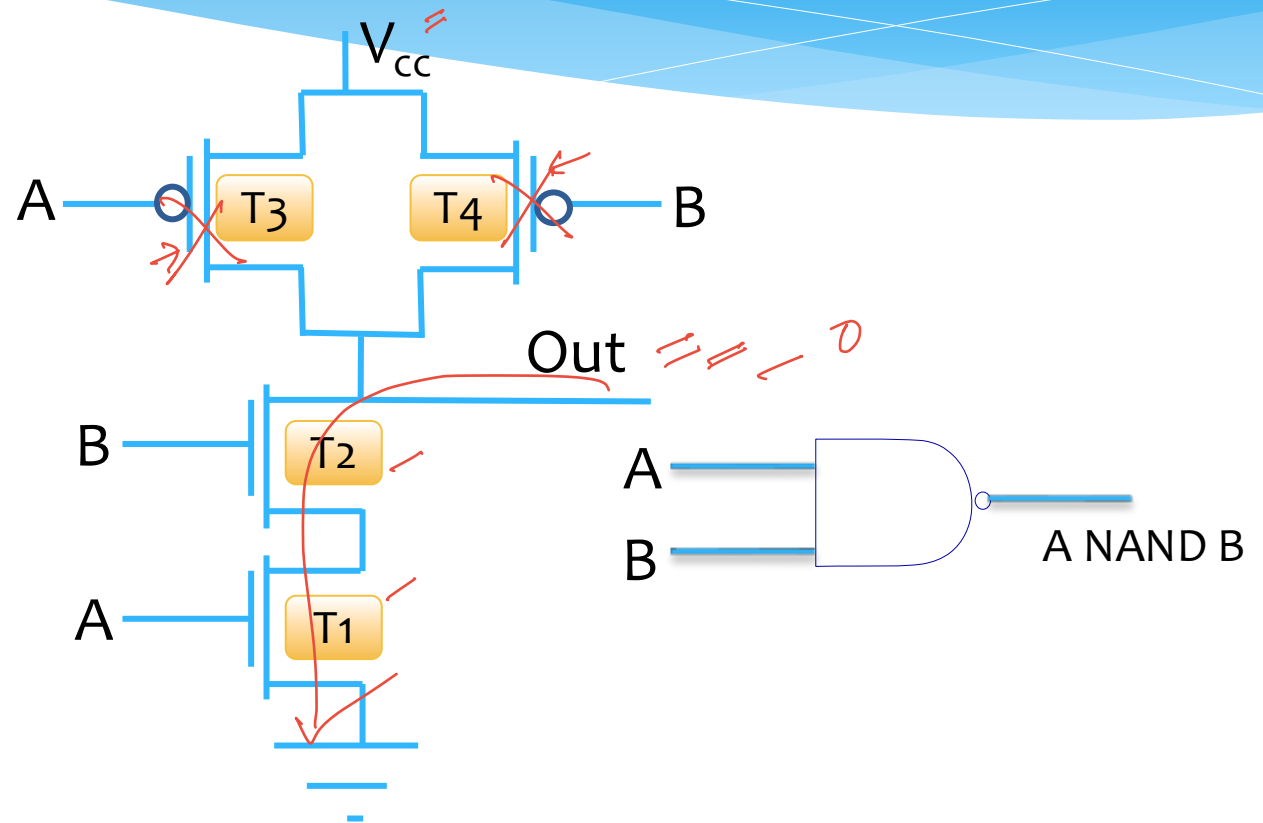
NOR Gate



A	B	T1	T2	T3	T4	Out
0	0	off	off	on	on	1
1	0	on	off	off	on	0
0	1	off	on	on	off	0
1	1	on	on	off	off	0

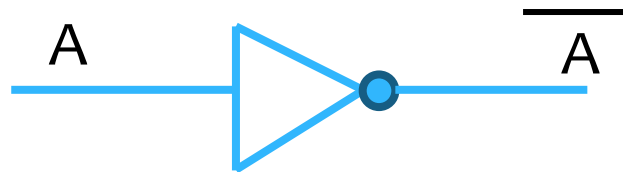
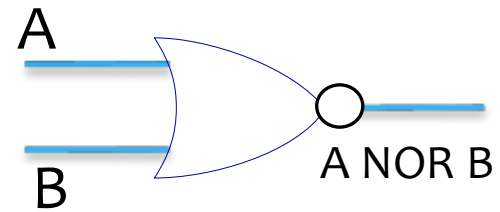
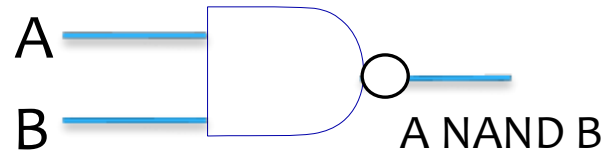
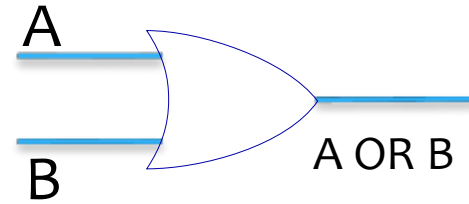
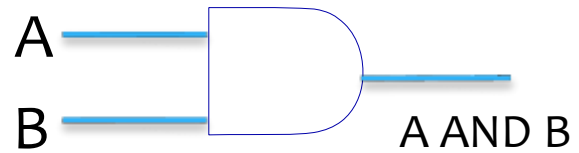
NAND		O/P
A	B	
0	0	1
0	1	1
1	0	1
1	1	0

NAND Gate



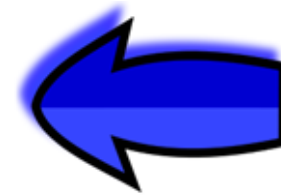
A	B	T1	T2	T3	T4	Out
0	0	off	off	on	on	1
1	0	on	off	off	on	1
0	1	off	on	on	off	1
1	1	on	on	off	off	0

Summary of Logic Gates



Outline

- *Transistors and Gates
- *Combinational Logic
- * Sequential Logic
- * SRAM/ DRAM Cells



Multiplexer

Given n **inputs**, choose one based on the **select** bits.

Example: Given 8 inputs, 3 select bits, choose 1 among them

